

IN THE CLAIMS

Please amend the following claims.

Claims 1-25 (cancelled)

26. (currently amended) A semiconductor device comprising:

a silicon substrate;

a patterned dielectric layer on the substrate, the patterned dielectric layer having a first hardness; and

a bulk metal layer comprising copper and beryllium, the bulk metal layer comprising a second hardness matching that of the first hardness of the patterned dielectric layer.

27. (currently amended) The device of claim 26 wherein beryllium is a finely dispersed solute rich phase precipitate.

28. (currently amended) The device of claim 26 wherein beryllium is part of a plurality of large grain precipitate islands.

29. (cancelled)

30. (new) The device of claim 26, wherein beryllium is in the approximate range of 0.1 and 10.0 atomic percent of the bulk metal layer.